

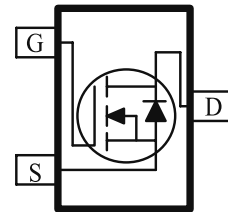
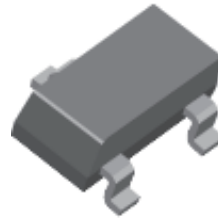
N-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low $r_{DS(on)}$ provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOT-23 saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ m(Ω)	I_D (A)
30	60 @ $V_{GS} = 4.5V$	3.5
	82 @ $V_{GS} = 2.5V$	3.0



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ C$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	Limit	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 12	
Continuous Drain Current ^a	$T_A = 25^\circ C$	I_D	3.5	A
	$T_A = 70^\circ C$		2.8	
Pulsed Drain Current ^b		I_{DM}	16	
Continuous Source Current (Diode Conduction) ^a		I_S	1.25	A
Power Dissipation ^a	$T_A = 25^\circ C$	P_D	1.3	W
	$T_A = 70^\circ C$		0.8	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^\circ C$

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$t \leq 10 \text{ sec}$	$R_{\theta JA}$	100	$^\circ C/W$
	Steady-State		166	$^\circ C/W$

Notes

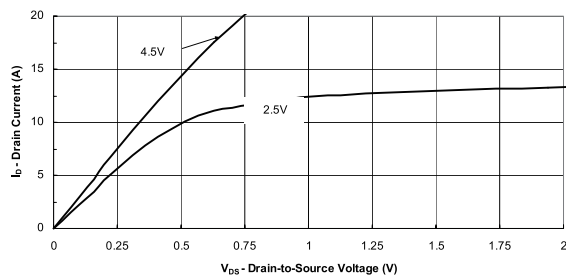
- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 uA	0.6	0.9	1.4	V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = 12 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24 V, V _{GS} = 0 V			1	uA
		V _{DS} = 24 V, V _{GS} = 0 V, T _J = 55°C			25	
On-State Drain Current ^A	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 4.5 V	6			A
Drain-Source On-Resistance ^A	r _{DS(on)}	V _{GS} = 4.5 V, I _D = 3.5 A			60	mΩ
		V _{GS} = 2.5 V, I _D = 3 A			82	
Forward Tranconductance ^A	g _{fs}	V _{DS} = 15 V, I _D = 3.5 A		6.9		S
Diode Forward Voltage	V _{SD}	I _S = 2.3 A, V _{GS} = 0 V		0.8		V
Dynamic ^b						
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 2.5 V, I _D = 3.5 A		6.3		nC
Gate-Source Charge	Q _{gs}			0.9		
Gate-Drain Charge	Q _{gd}			1.9		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 25 V, R _L = 25 Ω , I _D = 1 A, V _{GEN} = 10 V		16		nS
Rise Time	t _r			5		
Turn-Off Delay Time	t _{d(off)}			23		
Fall-Time	t _f			3		

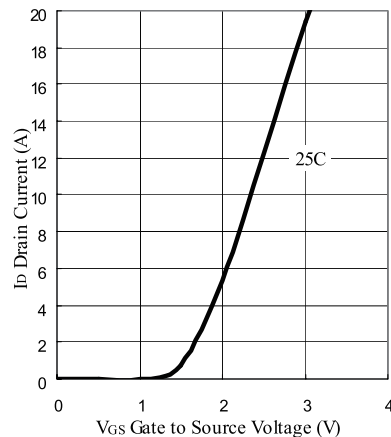
Notes

- Pulse test: $PW \leq 300\mu\text{s}$ duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.

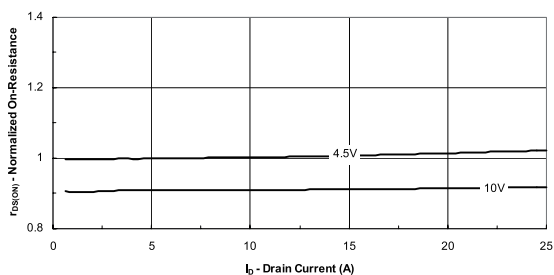
Typical Electrical Characteristics (N-Channel)



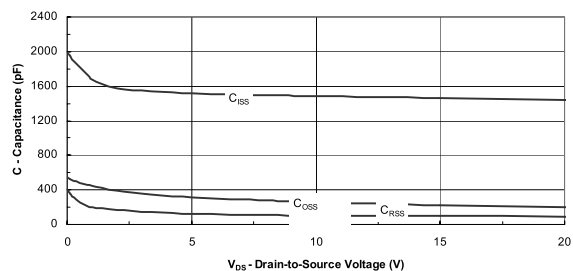
Output Characteristics



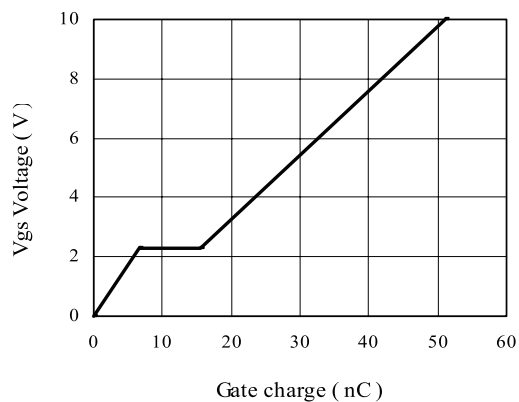
Transfer Characteristics



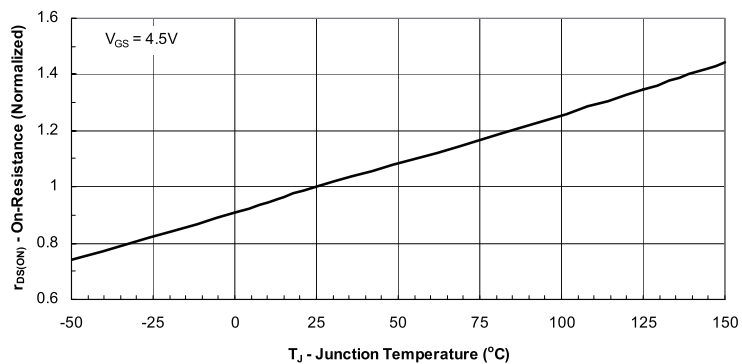
On-Resistance vs. Drain Current



Capacitance

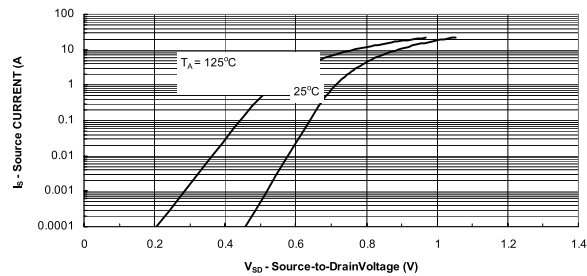


Gate Charge

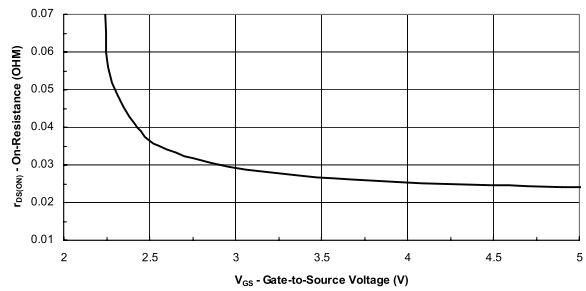
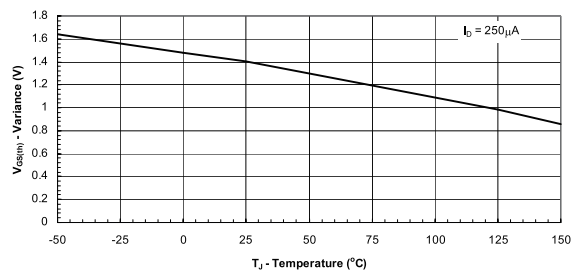


On-Resistance vs. Junction Temperature

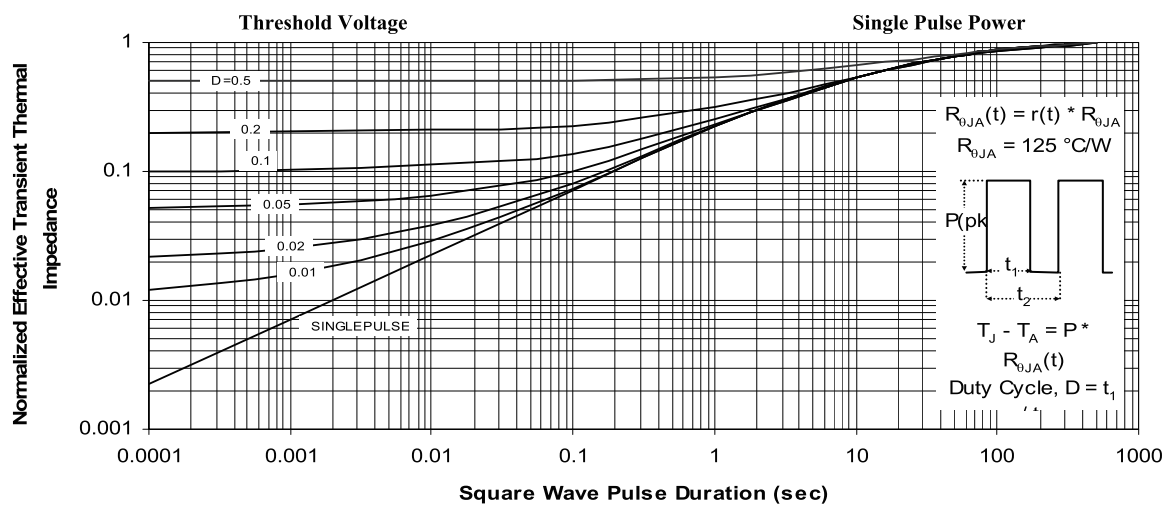
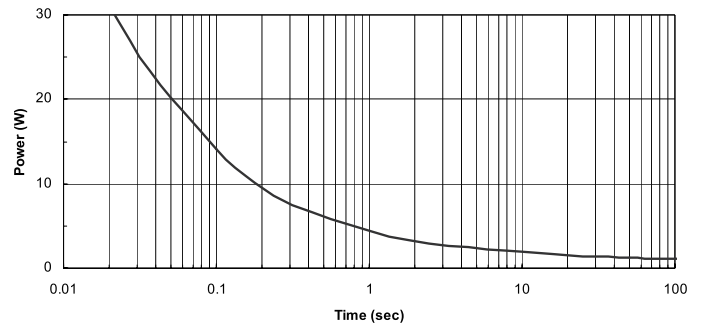
Typical Electrical Characteristics (N-Channel)



Source-Drain Diode Forward Voltage

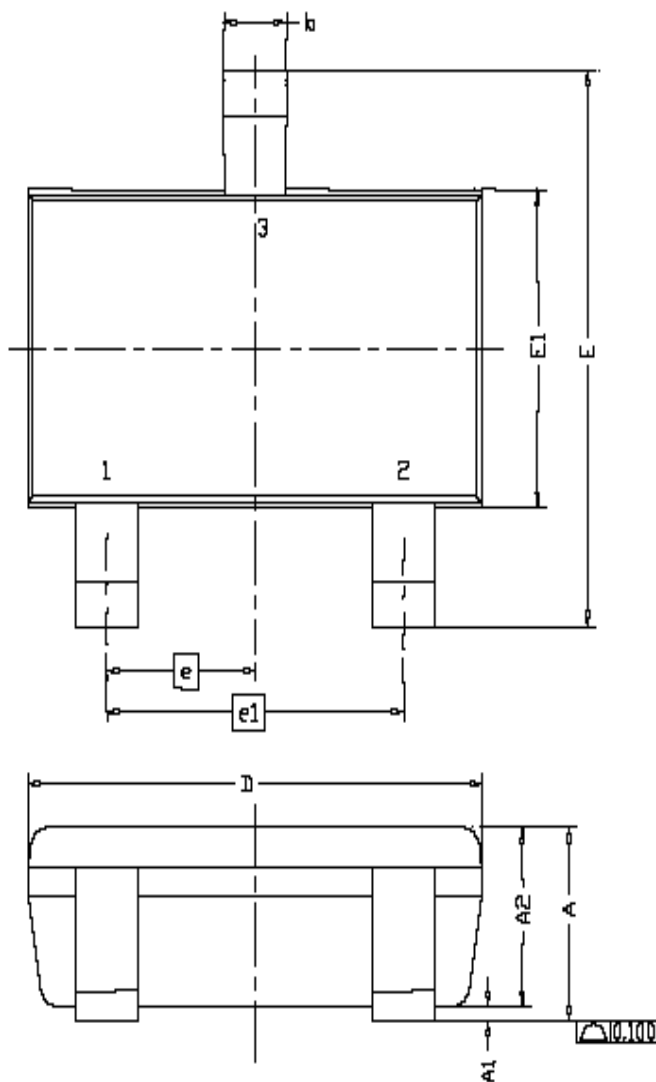


On-Resistance vs. Gate-to Source Voltage



Normalized Thermal Transient Impedance, Junction-to-Ambient

Package Information



DIM.	MILLIMETERS		
	MIN	NOM	MAX
A	0.935	0.95	1.10
A1	0.01	---	0.10
A2	0.85	0.90	0.925
b	0.30	0.40	0.50
c	0.10	0.15	0.25
D	2.70	2.90	3.10
E	2.60	2.80	3.00
E1	1.40	1.60	1.80
e	0.95 BSC		
e1	1.90 BSC		
L	0.30	0.40	0.60
L1	0.60 REF		
L2	0.25 BSC		
R	0.10	---	---
θ	0°	4°	8°
$\theta1$	7° NOM		

